
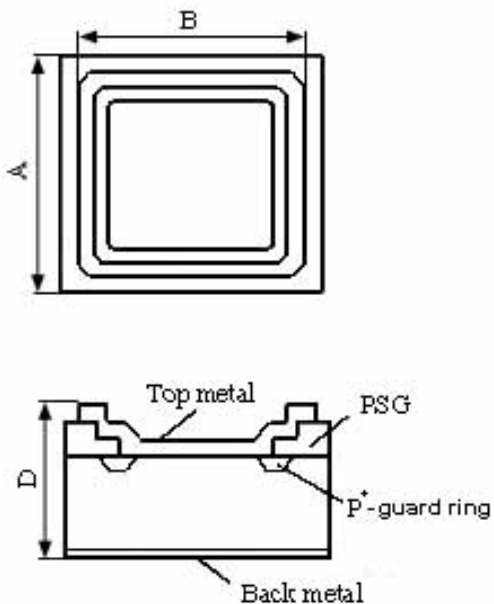


SCHOTTKY DIODE. KDN-30040.



Rev.1. Feb. 2010

 VSP-MIKRON	30A/40V. Die Size-106*158mil.			
Electrical Characteristics	Symbol	Unit	Spec. Limit	Die Sort
Breakdown Voltage @ $I_R=10mA$	V_{BR}	V	40	45
Average Rectified Forward Current	$I_{F(AV)}$	A	30,0	-
DC Forward Voltage @ 25°C, $I_F=30,0A$	V_F	V	0,57	0,55
Maximum Reverse Current @ 25°C, $V_R=45V$ 25°C, $V_R=40V$ 125°C, $V_R=40V$	I_R	mA	- 0,80 350	0,80 0,50 300,0
Peak Forward Surge Current 8,3ms single half sine-wave superimposed on rated load (JEDEC METHOD)	I_{FSM}	A	300	-
Peak Repetitive Reverse Surge Current @ 2,0µs, f=1kHz., $T_J<150°C$.	I_{RRM}	A	5,0	
Electrostatic Discharge Voltage. JEDEC Method. ESD HBM. Contact.	ESD	kV	±8 (contact)	
Voltage Rate of Change	dV/dt	V/µS	10.000	
Operating Junction Temperature	T_J	°C	150	



DIM	ITEM	µm
A_x A_y	Wafer Form Die Size	2700
		4000
B_x B_y	Top Metal Size	2560
		3860
D	Thickness	350max
Scribe line Width		80

Top metal: a) Ti-Ni-Ag – for Soldering;
b) Al.- for Wire Bonding.
Back metal: Ti-Ni-Ag.